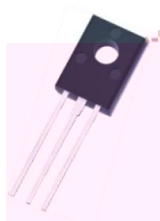
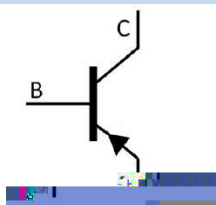


TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

I_C $V_{CE(sat)}$
High I_C , low $V_{CE(sat)}$.

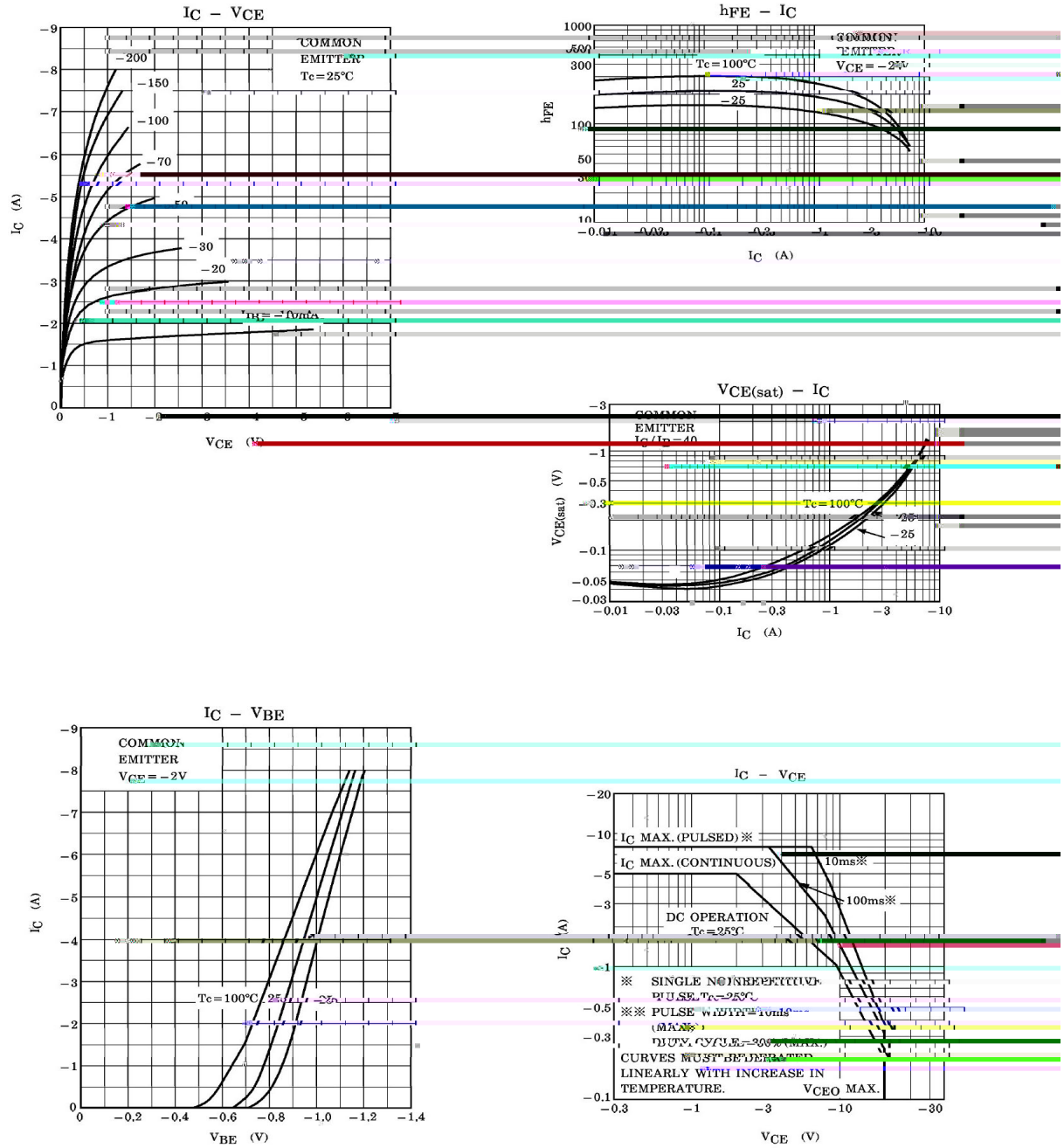
Strobe flash applications, audio power amplifier applications.

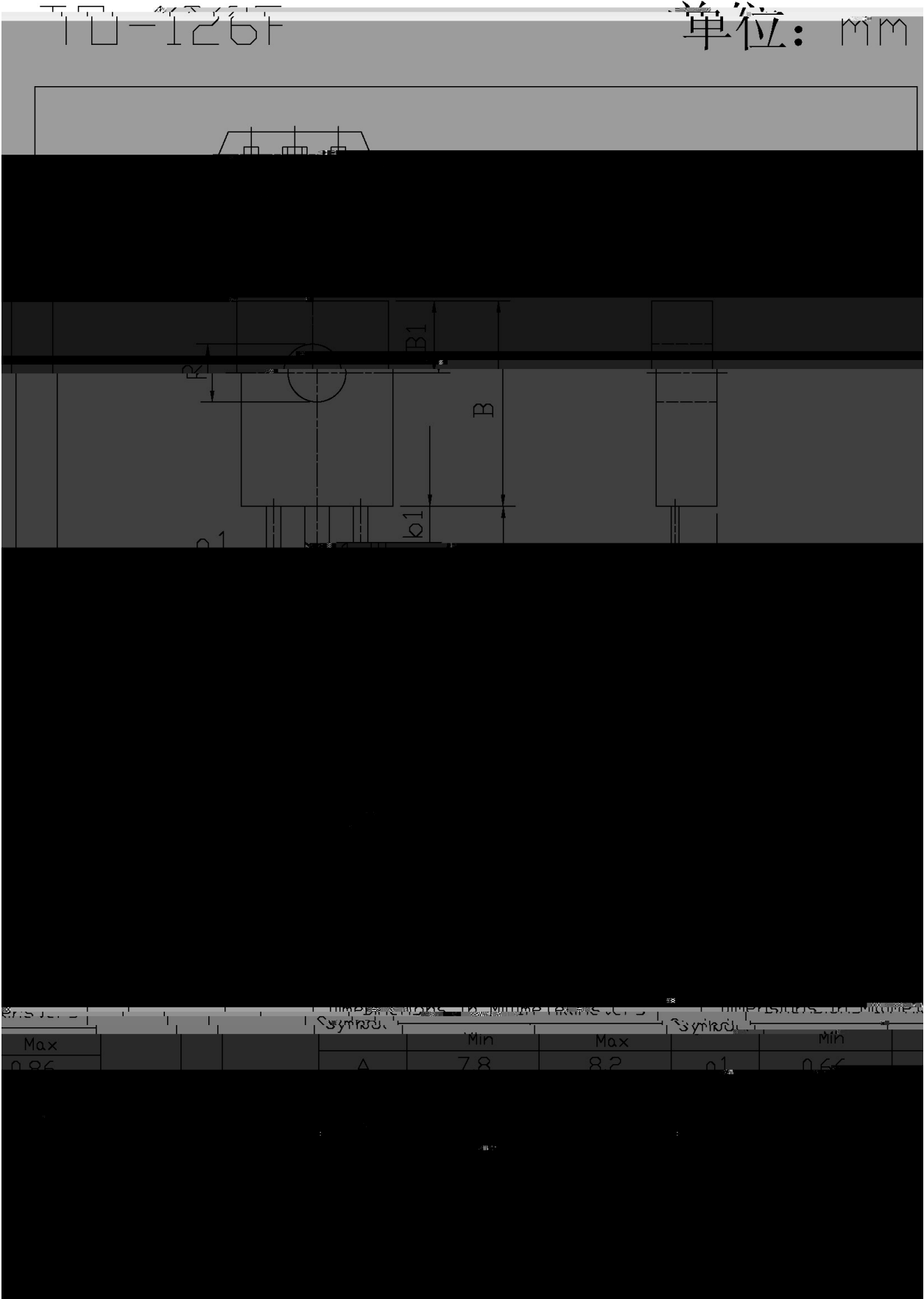


PIN1 Emitter PIN 2 Collector PIN 3 Base

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-8.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-8.0	A
Base Current – Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	10	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V					







BR

A1357

O: h_{FE}

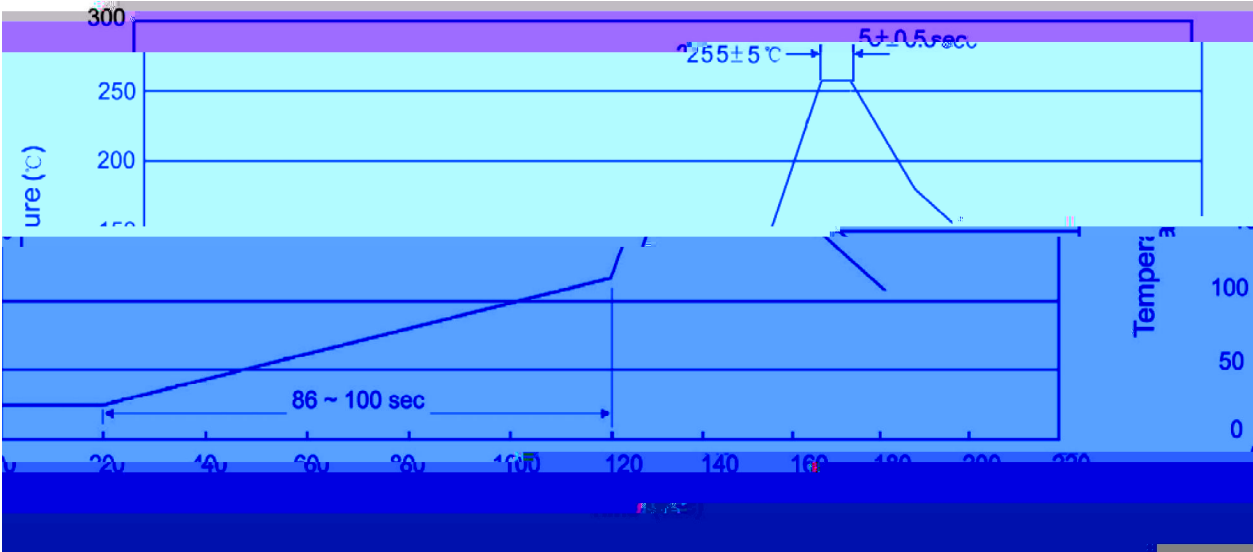
Note:

BR: Company Code

A1357: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- | | | | | |
|---|-------|-----|-----------|--------|
| 1 | 25 | 150 | 60 | 90sec; |
| 2 | 255±5 | | 5±0.5sec; | |
| 3 | | 2 | 10 | /sec. |

- Note:
- | | |
|------------------------|----------------------|
| 1.Preheating:25~150 | , Time:60~90sec. |
| 2.Peak Temp.:255±5 | , Duration:5±0.5sec. |
| 3. Cooling Speed: 2~10 | /sec. |

255±